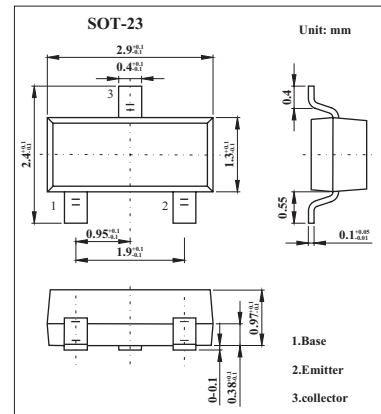


■ Features

- Collector Current:  $I_c = -1.5A$



■ Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_c$	-1.5	A
Collector Power Dissipation	$P_c$	0.3	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

■ Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_c = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_c = -100mA$	120		400	
		$V_{CE} = -1V, I_c = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -800mA, I_B = -80mA$			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_c = -1V, V_{CE} = -10mA$			-1	V
Base-emitter positive favor voltage	$V_{BEF}$	$I_B = -1A$			-1.55	V
output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Transition frequency	$f_T$	$V_{CE} = -10V, I_c = -50mA, f = 30MHz$	100			MHz

■ hFE Classification

Marking	Y2		
Rank	L	H	J
hFE	120~200	200~350	300~400

■ Typical Characteristics

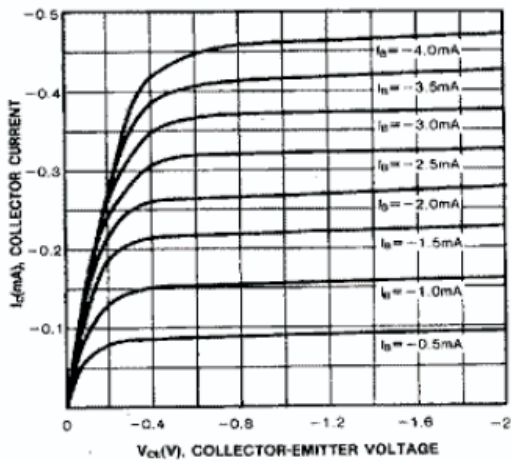


Fig.1 Static Characteristic

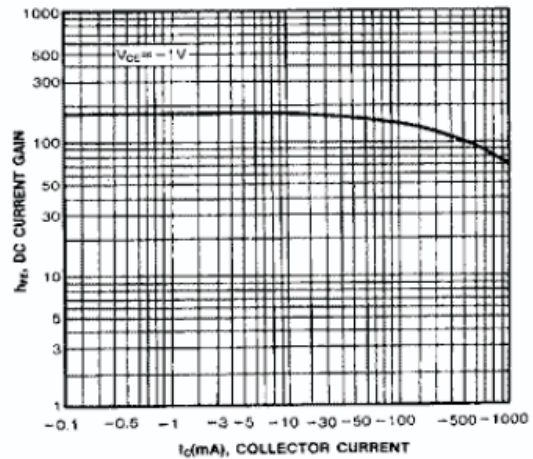


Fig.2 DC Current Gain

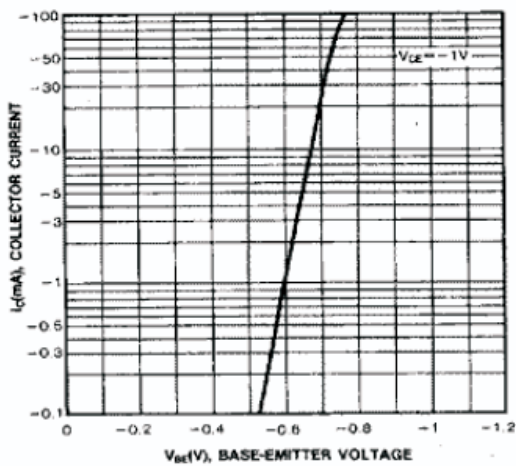


Fig.3 Base Emitter ON Voltage

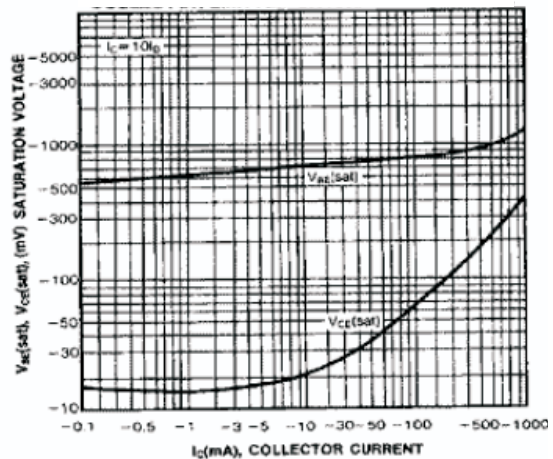


Fig.4 Base Emitter Saturation Voltage  
Collector Emitter Saturation Voltage

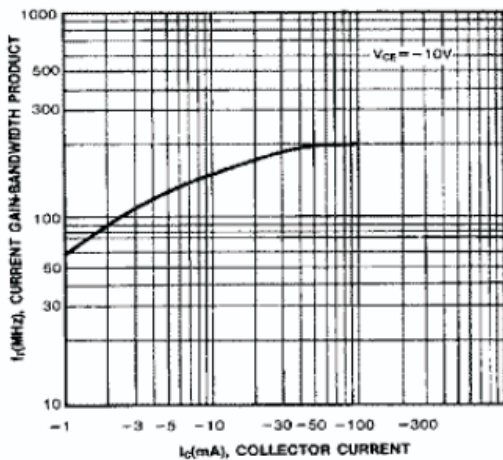


Fig.5 Current Gain Bandwidth Product

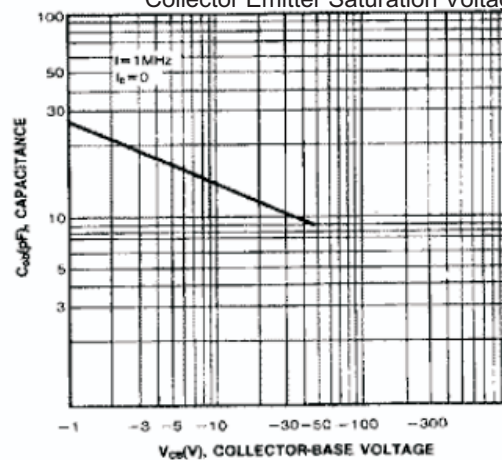


Fig.6 Collector Output Capacitance